RS2N65D

N Channel MOSFET

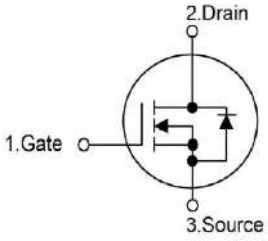
Lead Free Package and Finish

Applications:

- •Adapter & Charger
- •SMPS Standby Power
- •AC-DC Switching Power Supply
- •LED driving power

I_D	$R_{DS(ON)}$(Typ.)	V_{DSS}
2.0A	4.1Ω	650V

Not to Scale



Features:

- •Low On Resistance
- •Low Gate Charge
- •Peak Current vs Pulse Width Curve
- •RoHS Compliant

Ordering Information

Part Number	Package	Marking
RS2N65D	TO-252	RS2N65D

Absolute Maximun Ratings Tc=25℃ unless otherwise specified

Symbol	Parameter	RS2N65D	Units
V_{DSS}	Drain-to-Source Voltage (Note*1)	650	V
I_D	Continuous Drain Current	2.0	A
I_D@ 100 ℃	Continuous Drain Current	1.3	
I_{DM}	Pulsed Drain Current (Note*2)	6.0	
P_D	Power Dissipation	25	W
	Derating Factor above 25℃	0.28	W/℃
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Engergy L=30mH I_{AS}=2.52A V_{DD}=145V R_G=25Ω T_J=25℃	28.8	mJ
T_L	Maximum Temperature for Soldering	300	℃
T_{PKG}	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	260	
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	

*Drain Current Limited by Maximum Junction Temperature

Caution:Stresses greater than those listed in the“Absolute Maximum Ratings”Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS2N65D	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	4.92	℃/W	Drain lead soldered to water cooled heatsink,P_D adjusted for a peak junction temperature of +150℃.
$R_{\theta JA}$	Junction-to-Ambient	60		1 cubic foot chamber,free air.

OFF Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-source Breakdown Voltage	650	--	--	v	V_{GS}=0V,I_D=250μA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1.0	μA	V_{DS}=650V,V_{GS}=0V
I_{GSS}	Gate-to-Source Forward Leakage	--	--	100	nA	V_{GS}=+30V V_{DS}=0V
	Gate-to-Source Reverse Leakage	--	--	-100		V_{GS}=-30V V_{DS}=0V

ON Characteristics TJ=25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	--	4.1	4.8	Ω	V_{GS}=10V,I_D=1A
$V_{GS(TH)}$	Gate Threshold Voltage	3.0	--	4.0	V	V_{GS}=V_{DS},I_D=250μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	7.8	--	nS	V_{DS}=300V I_D=2.0A R_G=25Ω (Note:3,4)
t_{rise}	Rise Time	--	33	--		
$t_{d(OFF)}$	Turn-OFF Delay Time	--	23	--		
t_{fall}	Fall Time	--	59	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
C_{iss}	Input Capacitance	--	310	--	pF	V_{GS}=0V V_{DS}=25V f=1.0MHz
C_{oss}	Output Capacitance	--	39	--		
C_{rss}	Reverse Transfer Capacitance	--	6	--		
Q_g	Total Gate Charge	--	8	--	nC	V_{DS}=520V I_D=2.0A V_{GS}=10V (Note:3,4)
Q_{gs}	Gate-to-Source Charge	--	1.2	--		
Q_{gd}	Gate-to-Drain("Miller"）Charge	--	5	--		

Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current	--	--	2	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current	--	--	8	A	
V_{SD}	Diode Forward Voltage	--	--	1.4	V	I_S=2.0A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	80	--	nS	V_{GS}=0V I_S=2.0A,di/dt=100A/μs
Q_{rr}	Reverse Recovery Charge	--	1.8	--	μC	

Notes:

*1.TJ=±25℃ to +150℃.
*2.Repetitive rating;pulse width limited by maximum junction temperature.
*3.Pulse width≤300μs;duty cycle ≤1%.
*4.Basically not affected by temperature.

Typical Feature curve （TJ = 25° C, unless otherwise noted）

Figure 1. Output Characteristics

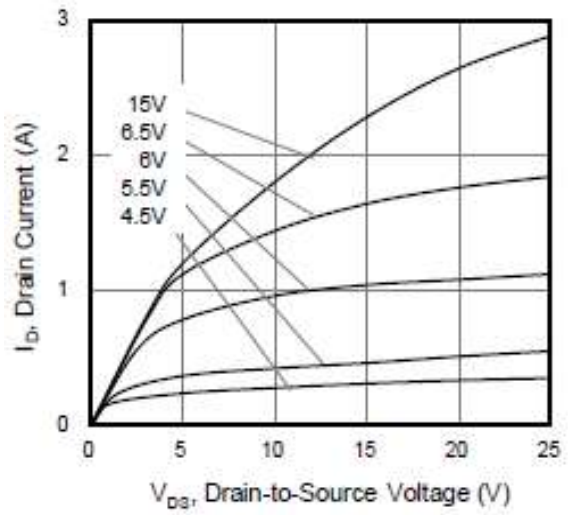


Figure 2. Drain Current vs. Temperature

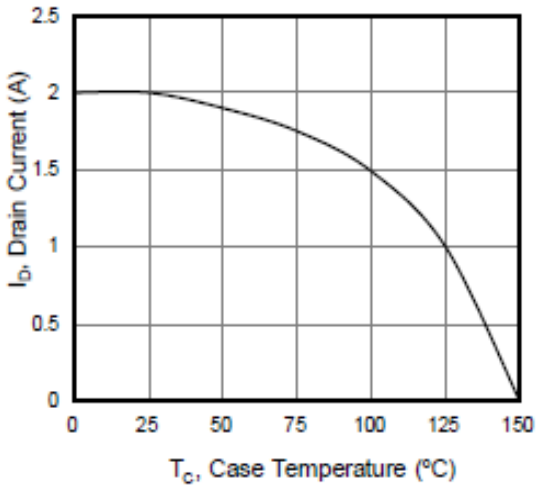


Figure 3. Body Diode Forward Voltage

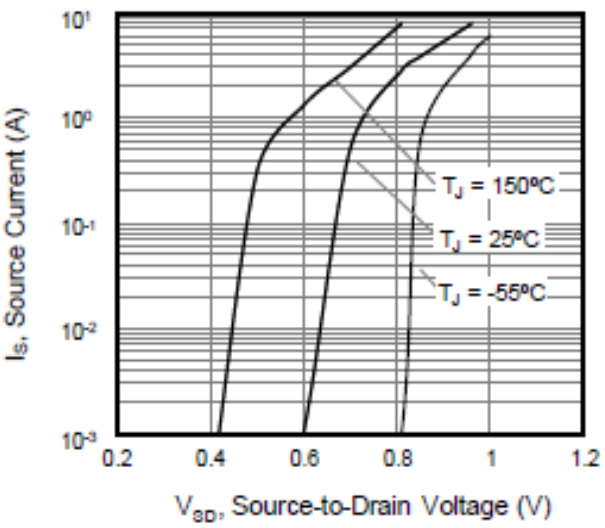


Figure 4. Power Dissipation vs. Temperature

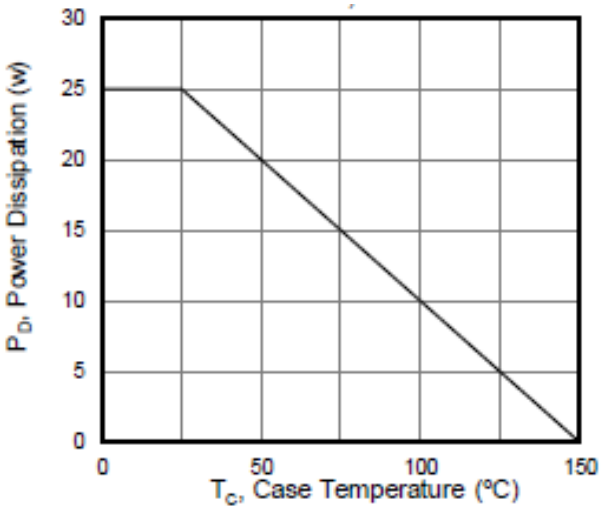


Figure 5. On-Resistance vs. Temperature

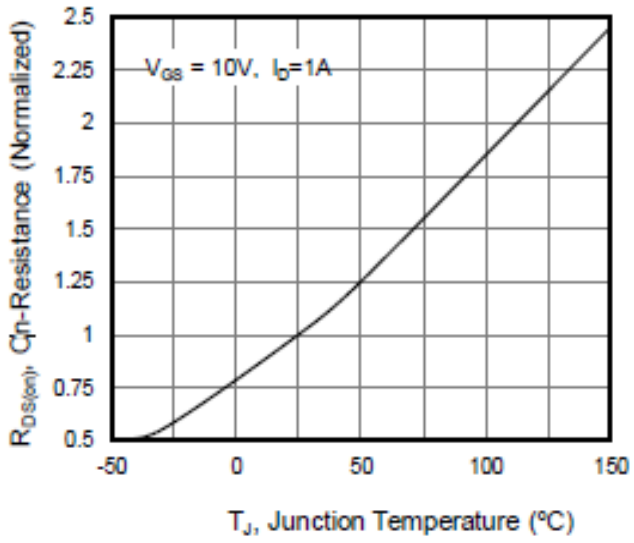


Figure 6. Transfer Characteristics

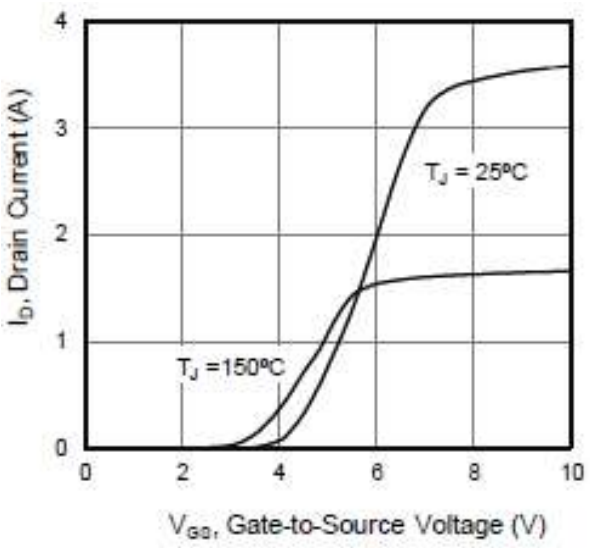


Figure7. Capacitance

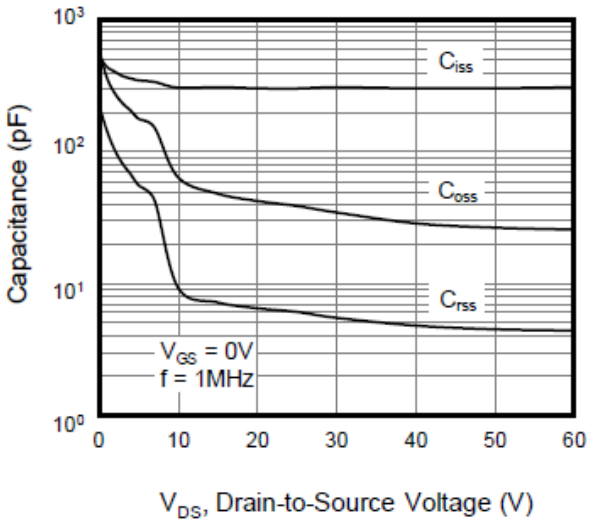


Figure8. Gate Charge

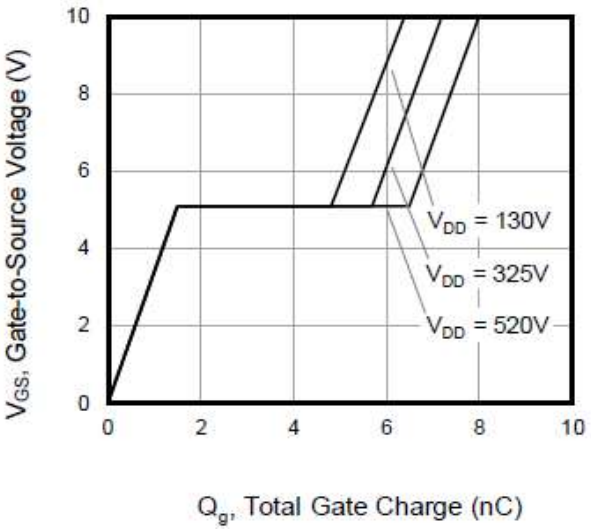
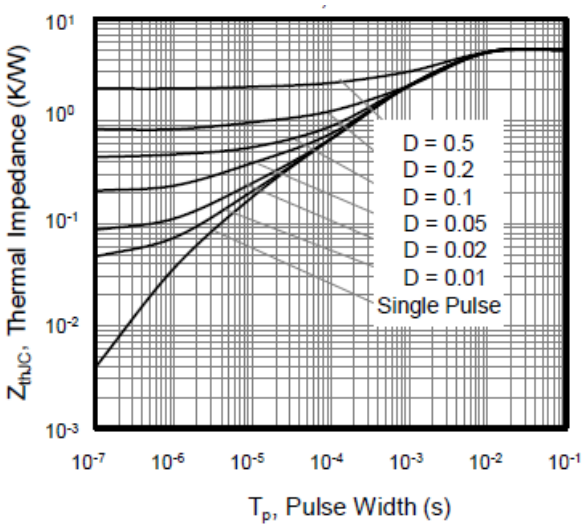


Figure 9. Transient Thermal Impedance
TO-252



Test Circuits and Waveforms

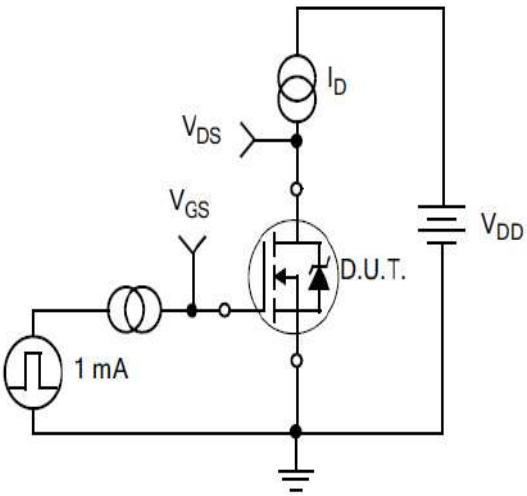


Figure10.
Gate Charge Test Circuit

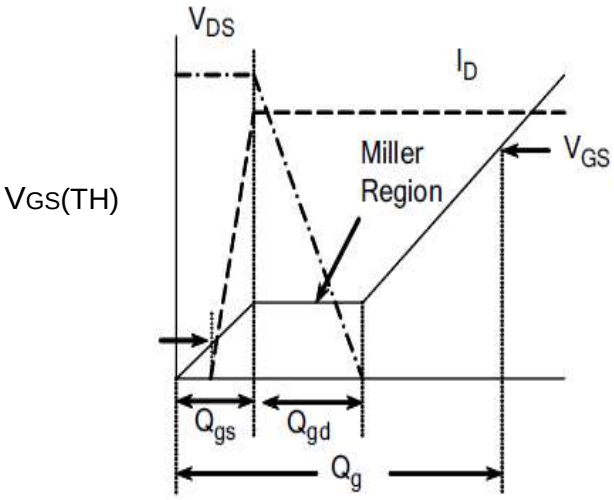


Figure11.
Gate Charge Waveform

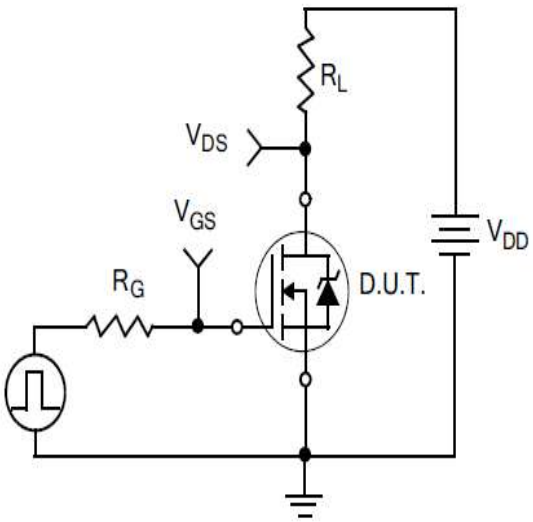


Figure12.
Resistive Switching Test Circuit

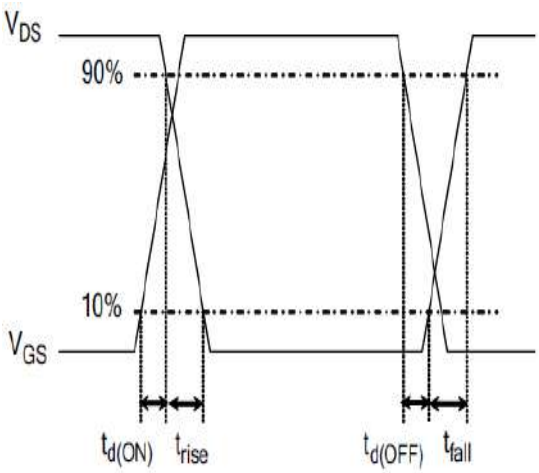


Figure13.
Resistive Switching Waveforms

Test Circuits and Waveforms

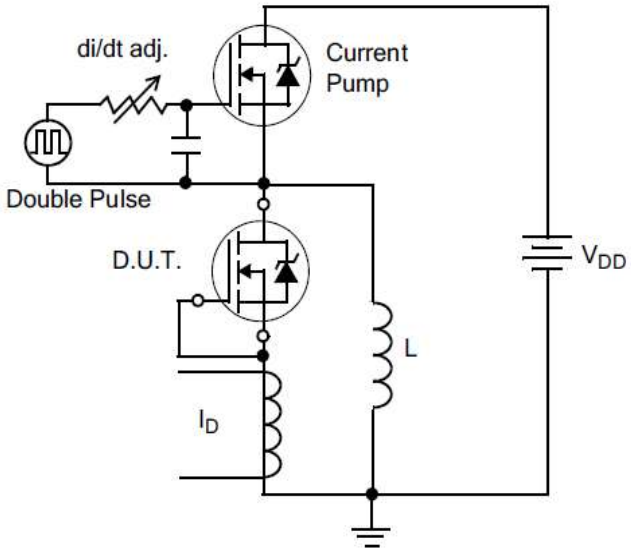


Figure14.Diode Reverse Recovery Test Circuit

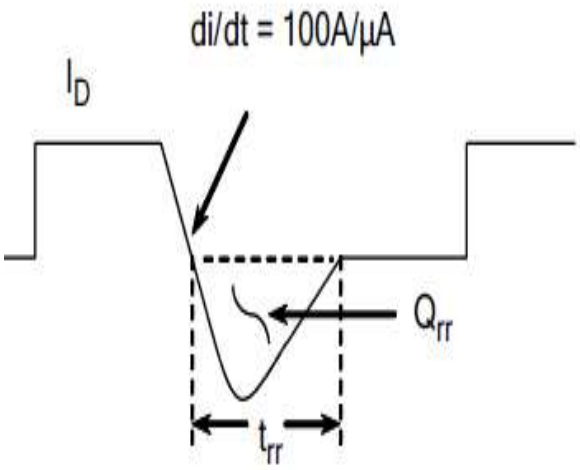


Figure15.Diode Reverse Recovery Waveform

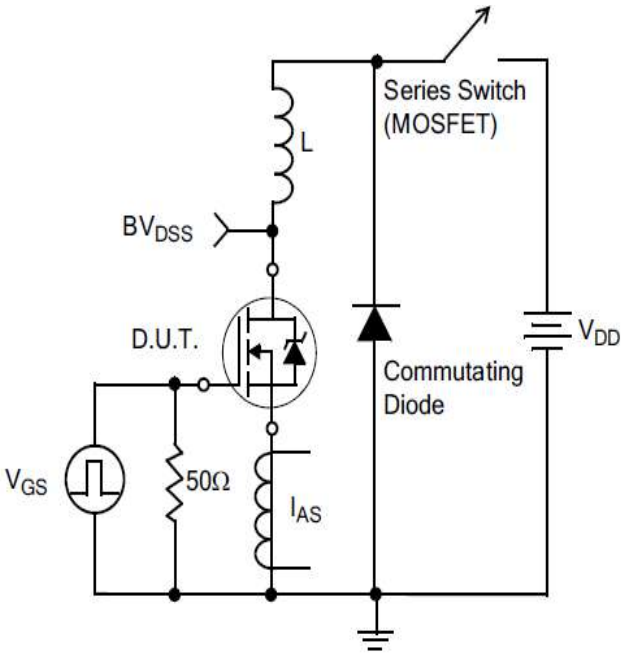
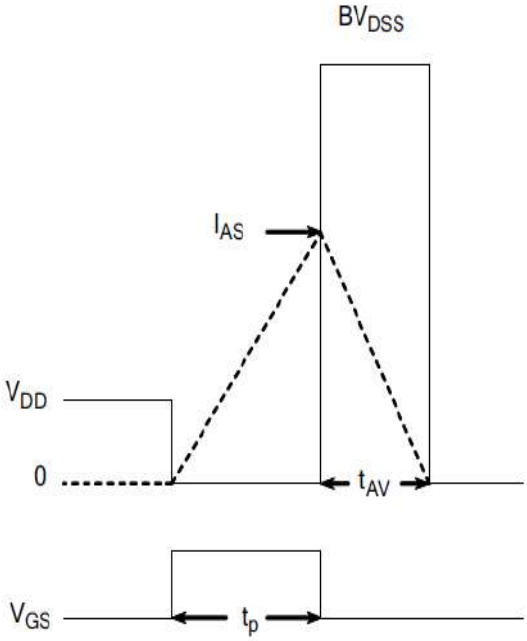


Figure16.Unclamped Inductive Switching Test Circuit

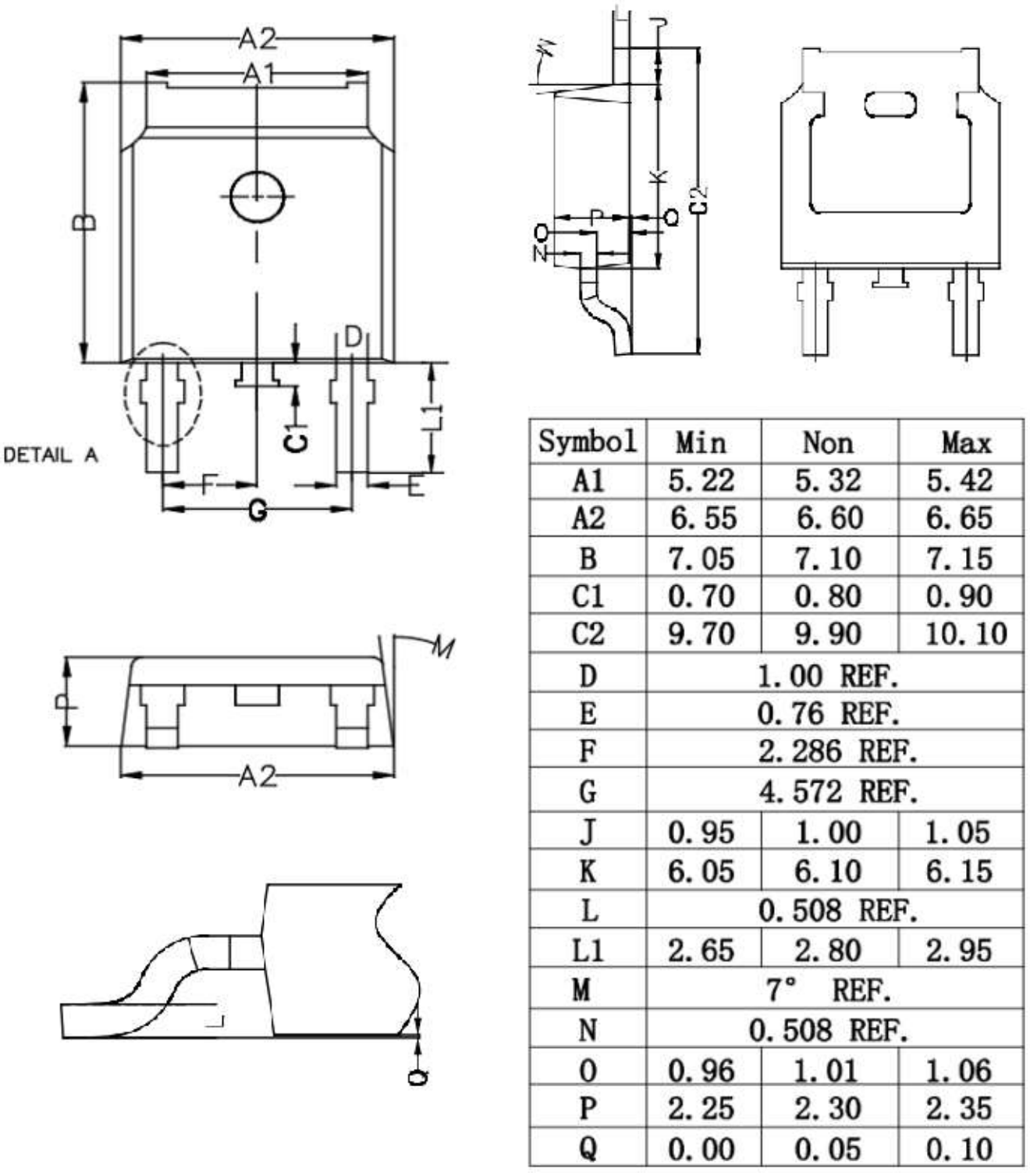


$$E_{AS}=\frac{I_{AS}^2 L}{2}$$

Figure17.Unclamped Inductive Switching Waveforms

Package outline drawing

Unit: mm



Symbol	Min	Non	Max
A1	5.22	5.32	5.42
A2	6.55	6.60	6.65
B	7.05	7.10	7.15
C1	0.70	0.80	0.90
C2	9.70	9.90	10.10
D		1.00 REF.	
E		0.76 REF.	
F		2.286 REF.	
G		4.572 REF.	
J	0.95	1.00	1.05
K	6.05	6.10	6.15
L		0.508 REF.	
L1	2.65	2.80	2.95
M		7° REF.	
N		0.508 REF.	
O	0.96	1.01	1.06
P	2.25	2.30	2.35
Q	0.00	0.05	0.10

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